

**SANYO**

No. 4355

**LB1817M****FDD Spindle Motor Driver****Overview**

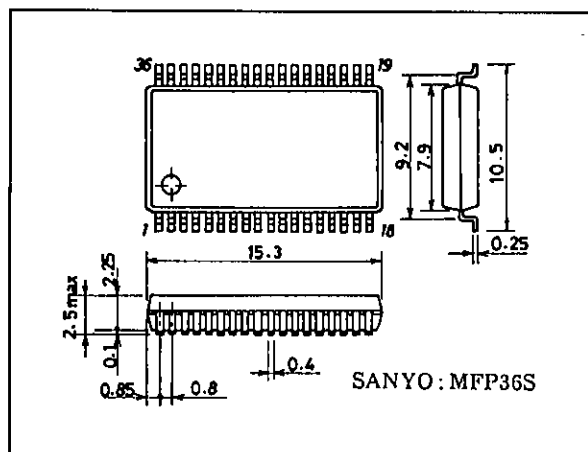
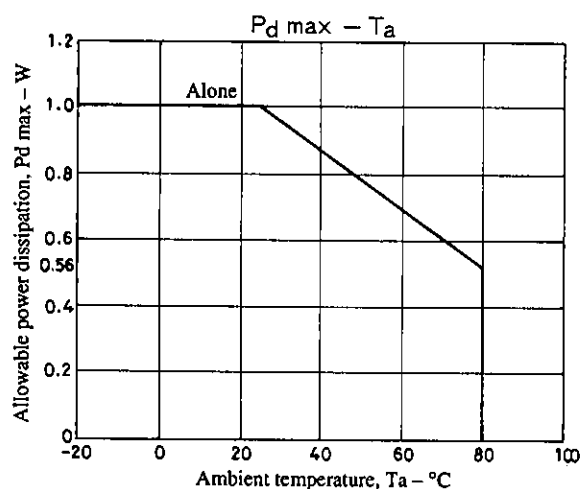
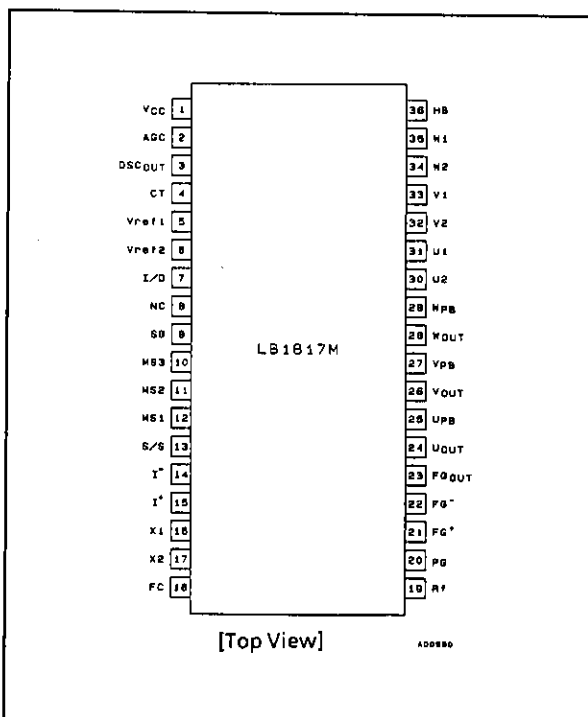
The LB1817M is the ideal IC for applications requiring a 5 V, low-profile FDD spindle motor driver.

**Functions and Features**

- Three phase total wave linear driver (external PNP)
- Low saturation voltage
- On-chip digital speed control
- Start/stop circuit ("L" level active)
- Rotation speed switching
- Current limiter circuit
- On-chip index processing circuit
- Index timing supports adjustments using VR
- AGC circuit
- Temperature protection circuit

**Package Dimensions**

unit : mm

**3129-MFP36S****Allowable power dissipation vs. ambient temperature****Pin Assignment****SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

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20593TS A8-9155 No.4355-1/9

## Specifications

### Absolute Maximum Ratings at Ta = 25°C

			unit
Maximum supply voltage	V <sub>CC</sub> max	7.0	V
Maximum output current	I <sub>CC</sub> max1	1.5	A
Steady maximum output current	I <sub>O</sub> max2	1.0	A
Allowable power dissipation	Pd max	1	W
Operating temperature	Topr	-20 to +80	°C
Storage temperature range	Tstg	-40 to +150	°C

### Allowable Operating Conditions at Ta = 25°C

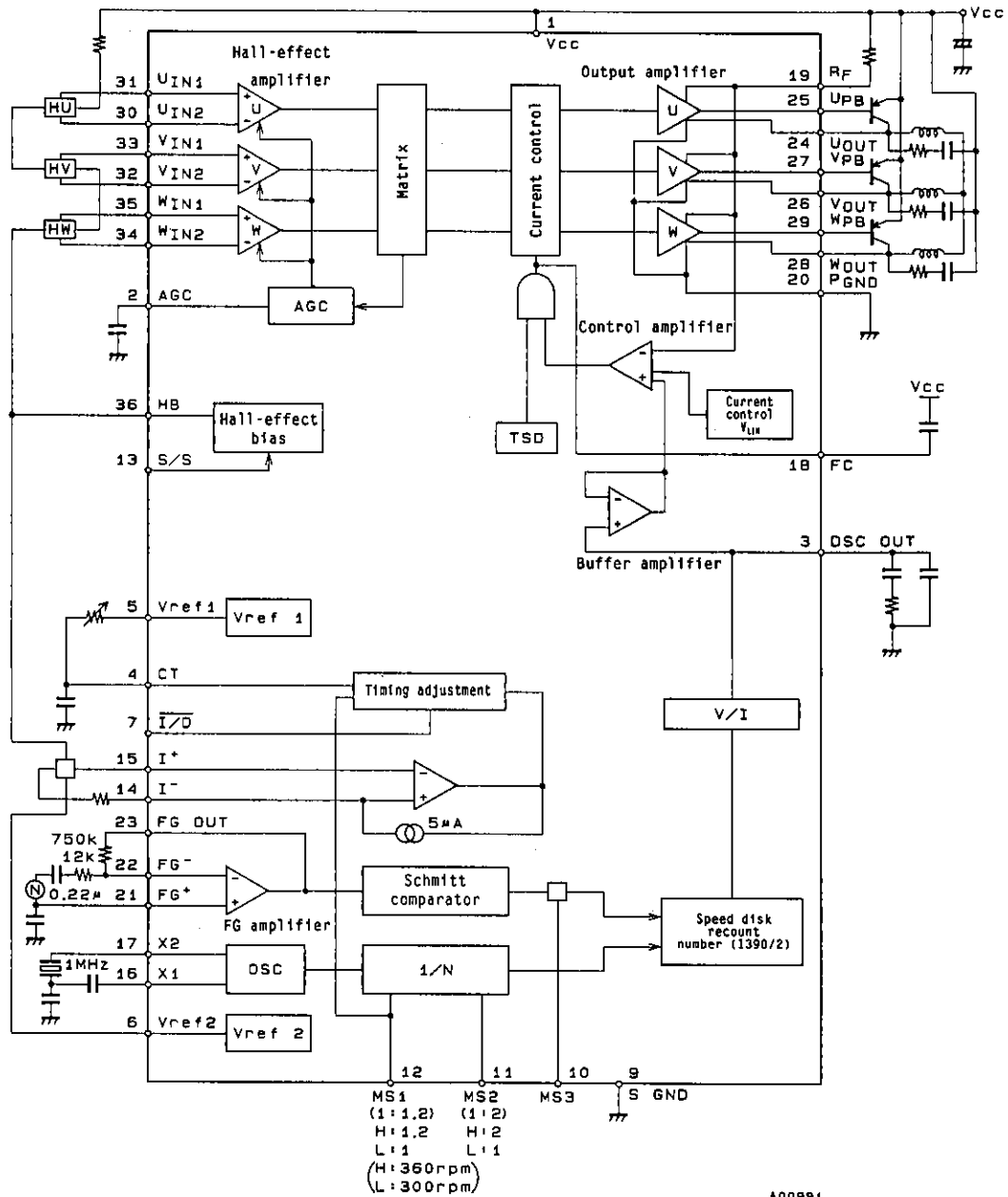
			unit
Supply voltage	V <sub>CC</sub>	4.2 to 6.5	V

### Electrical Characteristics at Ta = 25°C, V<sub>CC</sub> = 5V

		min	typ	max	unit	note
Current consumption	I <sub>CCO</sub>		70	100	μA	
	I <sub>CC</sub>		25	35	mA	
MS1 bias current	I <sub>MS1</sub>		180	270	μA	
MS1 "L" level input voltage	V <sub>MS1L</sub>	0		0.8	V	
MS1 "H" level input voltage	V <sub>MS1H</sub>	2.0		V <sub>CC</sub>	V	
MS2 bias current	I <sub>MS2</sub>		90	135	μA	
MS2 "L" level input voltage	V <sub>MS2L</sub>	0		0.8	V	
MS2 "H" level input voltage	V <sub>MS2H</sub>	2.0		V <sub>CC</sub>	V	
MS3 bias current	I <sub>MS3</sub>		90	135	μA	
MS3 "L" level input voltage	V <sub>MS3L</sub>	0		0.8	V	
MS3 "H" level input voltage	V <sub>MS3H</sub>	2.0		V <sub>CC</sub>	V	
S/S bias current	I <sub>S/S</sub>			20	μA	
S/S "L" level voltage	V <sub>S/SL</sub>	0		0.8	V	
S/S "H" level voltage	V <sub>S/SH</sub>	2.0		V <sub>CC</sub>	V	
Hall-effect bias amplifier input current	I <sub>HB</sub>			15	μA	
In-phase input voltage range	V <sub>h</sub>	2.0		V <sub>CC</sub> - 0.7	V	
Differential input voltage range	V <sub>dif</sub>	50		200	mVp-p	
Input offset voltage	V <sub>ho</sub>			±10	mV	*
Hall-effect output voltage	V <sub>H</sub>	0.5	0.8	1.1	V	
Leak current	I <sub>HL</sub>			±10	μA	
Output saturation voltage	V <sub>sat</sub>		0.45	0.64	V	
Output leak current	I <sub>OL</sub>			1.0	mA	
Current limiter	I <sub>lim</sub>	6.3	7.5	8.7	mA	
Control amplifier voltage gain	G <sub>C</sub>	-7.5	-5.5	-3.5	dB	
Voltage gain phase differential	ΔG <sub>C</sub>			±1	dB	
V/I conversion source current	I <sup>+</sup>	19	28	37	μA	
V/I conversion sink current	I <sup>-</sup>	-19	-28	-37	μA	
V/I conversion current ratio	I <sup>+</sup> /I <sup>-</sup>	0.8	1.0	1.2		
DSC buffer input current	I <sub>DSC</sub>			1.0	μA	
FG amplifier input voltage	V <sub>FG</sub>	2		20	mVp-p	
FG amplifier voltage gain	G <sub>FG</sub>		60		dB	*
FG amplifier input offset	V <sub>FGO</sub>			±10	mV	*
FG amplifier internal reference voltage	V <sub>RGB</sub>	2.2	2.5	2.8	V	
FG schmitt hysteresis width	ΔV <sub>sh1</sub>		25		mV	*
	ΔV <sub>sh2</sub>		25		mV	*
Speed disk recount number	N		1390/2			
Disk operation frequency	F <sub>D</sub>			1.1	MHz	*
Oscillation range	F <sub>OSC</sub>			1.1	MHz	*
Oscillation frequency error	ΔF <sub>OSC</sub>			±0.2	%	
Index output "L" level voltage	V <sub>IDL</sub>			0.4	V	
Index output leak current	I <sub>IDL</sub>			±10	μA	
Index amplifier in-phase input voltage range	V <sub>i</sub>	0.2		V <sub>CC</sub> - 0.7	V	
Index amplifier differential input voltage range	V <sub>DIF</sub>	25		100	mV	
Index amplifier hysteresis setting current	I <sub>HYS</sub>	2.9	4.2	5.5	μA	
Timing adjustment "H" level	V <sub>TH</sub>	1.15	1.26	1.35	V	
Timing adjustment "L" level	V <sub>TL</sub>	0.4	0.52	0.6	V	
Timing adjustment ratio	T <sub>HL</sub>		1.148			
Reference voltage	V <sub>REF1</sub>	2.20	2.50	2.80	V	
	V <sub>REF2</sub>	1.85	2.15	2.45	V	
Excessive heat protected operating temperature	TSD	150	180		°C	*
Hysteresis width	ΔTSD		10		°C	*

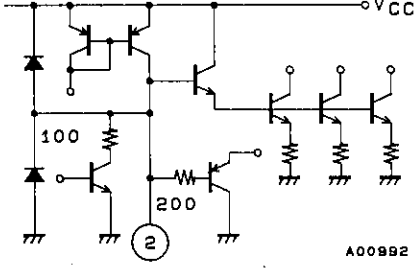
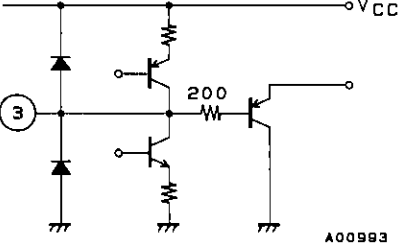
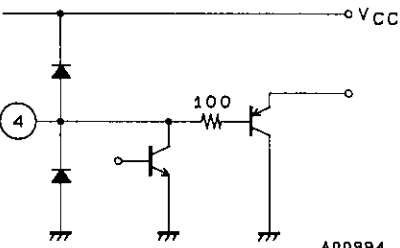
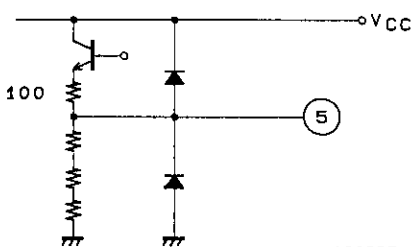
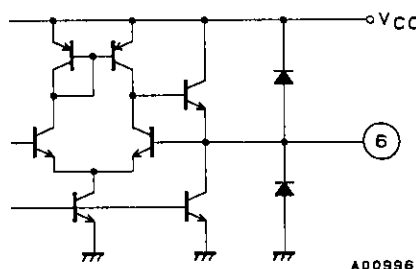
Note: Marked values (\*) are guaranteed by the design itself and therefore do not require measurement.

## Block Diagram



Unit (resistance: Ω, capacitance: F)

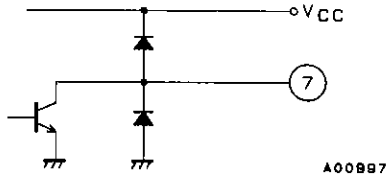
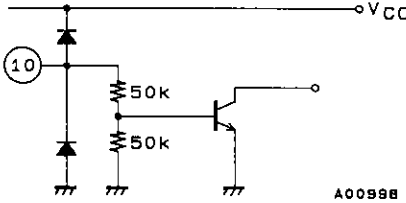
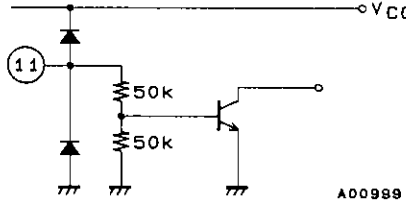
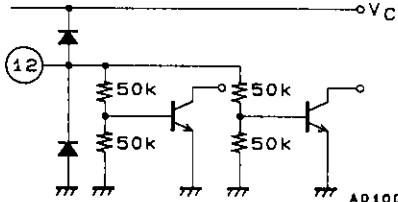
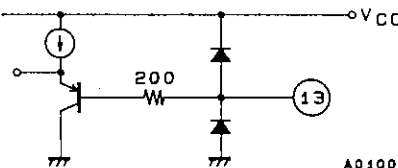
## Pin Description

Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
1	V <sub>CC</sub>			<ul style="list-style-type: none"> <li>Power supply voltage pin. Voltage must be stable and free of ripple noise interference.</li> </ul>
2	AGC		 <p>A00992</p>	<ul style="list-style-type: none"> <li>AGC pin. Controls hall-effect amplifier gain in response to hall-effect input frequency. External capacitor installation.</li> </ul>
3	DSC out		 <p>A00993</p>	<ul style="list-style-type: none"> <li>Speed discriminator pin.</li> </ul>
4	CT		 <p>A00994</p>	<ul style="list-style-type: none"> <li>Timing adjustment pin. External CR for delay time constant connected.</li> </ul>
5	Vref1	2.5V typ	 <p>A00995</p>	<ul style="list-style-type: none"> <li>Vref1 pin. Used as external CR power supply for index timing adjustment applications.</li> </ul>
6	Vref2	2.15V typ	 <p>A00996</p>	<ul style="list-style-type: none"> <li>Vref2 pin. Used for sensor bias for external index applications.</li> </ul>

Unit (resistance:  $\Omega$ )

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Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
7	I/D			<ul style="list-style-type: none"> <li>Index pulse output pin.</li> </ul>
8	NC			<ul style="list-style-type: none"> <li>No connection.</li> </ul>
9	GND			<ul style="list-style-type: none"> <li>Ground pin for signal system. Grounded as with pin 20.</li> </ul>
10	MS3	H: 2.0V min L: 0.8V max		<ul style="list-style-type: none"> <li>FG changeover pin. When operating at an "H" level, FG sets to a through state. An "L" level results in 1-step division of FG.</li> </ul>
11	MS2	H: 2.0V min L: 0.8V max		<ul style="list-style-type: none"> <li>CLK changeover pin. When operating at an "H" level, CLK sets to a through state. An "L" level results in 1-step division of CLK.</li> </ul>
12	MS1	H: 2.0V min L: 0.8V max		<ul style="list-style-type: none"> <li>Rotation speed changeover pin. An "H" level sets rotation speed to 360 rpm. An "L" level sets rotation speed to 300 rpm. For more details, refer to the rotation speed changeover table.</li> </ul>
13	S/S	H: 2.0V min L: 0.8V max		<ul style="list-style-type: none"> <li>Start/stop changeover pin. "L" level active.</li> </ul>

Unit (resistance:  $\Omega$ )

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Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
14 15	I <sup>-</sup> I <sup>+</sup>		<p style="text-align: right;">A01002</p>	<ul style="list-style-type: none"> <li>External index negative input pin.</li> <li>External index positive input pin.</li> </ul> <p>When the I<sup>-</sup> pin is at an "H" level, I1 operates with the fixed current; at an "L" level, I1 does not flow.</p> <p>Hysteresis width is determined by the resistor attached externally to the I<sup>-</sup> pin.</p>
16	X1		<p style="text-align: right;">A01003</p>	<ul style="list-style-type: none"> <li>Reference clock generating pin.</li> </ul>
17	X2		<p style="text-align: right;">A01004</p>	
18	FC		<p style="text-align: right;">A01005</p>	<ul style="list-style-type: none"> <li>Frequency characteristics revision pin</li> </ul> <p>By installing a capacitor between this pin and V<sub>CC</sub>, close-loop oscillation for the current control system halts.</p>
19	RF			<ul style="list-style-type: none"> <li>Output current detection pin.</li> </ul> <p>By installing an R<sub>f</sub> resistor between this pin and V<sub>CC</sub>, output current is detected as voltage. Voltage detection at this pin activates the current limiter.</p> <p>Detection level is approximately 1/50 of output current.</p>
20	PGND			<ul style="list-style-type: none"> <li>Output transistor grounding pin.</li> </ul> <p>Grounded as with pin 9.</p>

Unit (resistance: Ω)

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Unit (resistance:  $\Omega$ )

Pin Number	Pin Symbol	Pin Voltage	Equivalent Circuit	Pin Description
21 22	FG+ FG-	2.5V typ	<p style="text-align: right;">A01006</p>	<ul style="list-style-type: none"> <li>• FG amplifier positive pin.</li> <li>• FG amplifier negative pin.</li> </ul>
23	FG out		<p style="text-align: right;">A01007</p>	<ul style="list-style-type: none"> <li>• FG amplifier output pin.</li> </ul>
24 25 26 27 28 29	U <sub>OUT</sub> U <sub>PB</sub> V <sub>OUT</sub> V <sub>PB</sub> W <sub>OUT</sub> W <sub>PB</sub>		<p style="text-align: right;">A01008</p>	<ul style="list-style-type: none"> <li>• U-phase output pin.</li> <li>• Base connection pin for U-phase external PNP.</li> <li>• V-phase output pin.</li> <li>• Base connection pin for V-phase external PNP.</li> <li>• W-phase output pin.</li> <li>• Base connection pin for W-phase external PNP.</li> </ul>
30 31 32 33 34 35	U <sub>IN2</sub> U <sub>IN1</sub> V <sub>IN2</sub> V <sub>IN1</sub> W <sub>IN2</sub> W <sub>IN1</sub>		<p style="text-align: right;">A01009</p>	<ul style="list-style-type: none"> <li>• U-phase hall-effect input pin. U<sub>IN1</sub> &gt; U<sub>IN2</sub> is established when logic is at an "H" level.</li> <li>• V-phase hall-effect input pin. V<sub>IN1</sub> &gt; V<sub>IN2</sub> is established when logic is at an "H" level.</li> <li>• W-phase hall-effect input pin. W<sub>IN1</sub> &gt; W<sub>IN2</sub> is established when logic is at an "H" level.</li> </ul>
36	HB		<p style="text-align: right;">A01010</p>	<ul style="list-style-type: none"> <li>• Hall-effect bias applied to minus-side pin. When stopped, switches open and hall-effect bias severs.</li> </ul>

Truth Table

	Source → Sink	Hall-Effect Input		
		U	V	W
1	V-phase → W-phase	H	H	L
2	V-phase → U-phase	L	H	L
3	W-phase → U-phase	L	H	H
4	W-phase → V-phase	L	L	H
5	U-phase → V-phase	H	L	H
6	U-phase → W-phase	H	L	L

When an "H" level exists for hall-effect input,

$$U_{IN1} > U_{IN2}$$

$$V_{IN1} > V_{IN2}$$

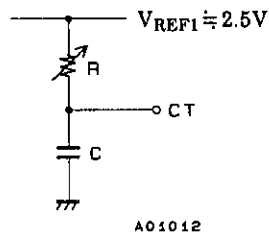
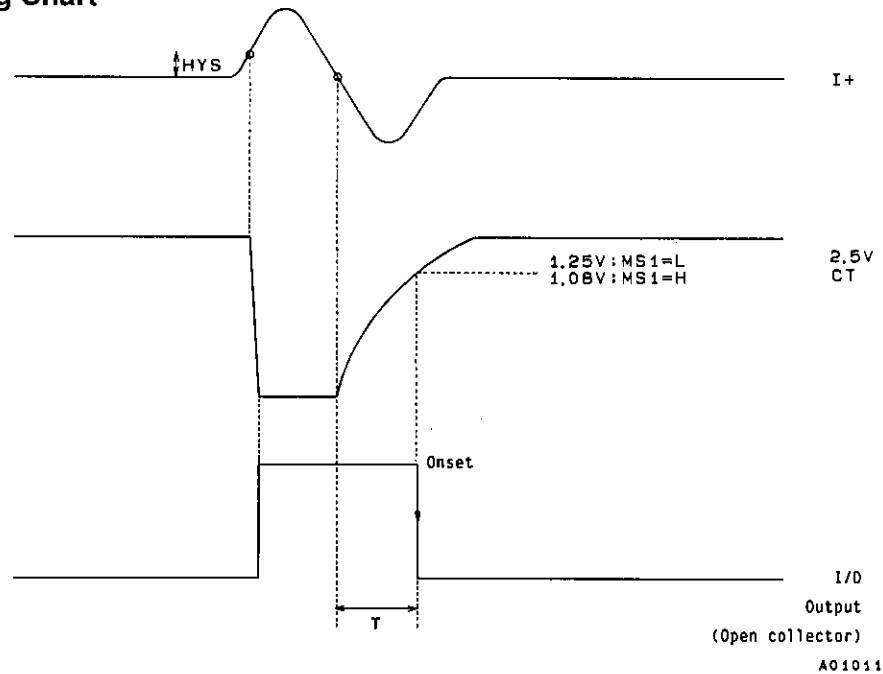
$$W_{IN1} > W_{IN2}$$

Rotation Speed Changeover Table

$$f_{OSC} = 1\text{MHz}$$

MS1	H	L	H	L	H	L	H	L
MS2	H		L		H		L	
MS3	H		L		L		H	
$f_{FG}$ [Hz]	720	600	720	600	1440	1200	360	300

Index and Timing Chart



$$T \approx 0.693CR \dots \text{MS1} = \text{L}$$

$$T \approx 0.836CR \dots \text{MS1} = \text{H}$$

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